

DESCRIPTION

The MP1924 is a high-frequency, 100V, half-bridge, N-channel, power MOSFET driver. Its low-side and high-side driver channels are independently controlled and matched with less than 5ns in time delay. Under-voltage lockout on both high-side and low-side supplies force their outputs low in case of insufficient supply. The integrated bootstrap diode reduces external component count.

FEATURES

- Drives an N-Channel MOSFET Half Bridge
- 118V V_{BST} Voltage Range
- On-Chip Bootstrap Diode
- Typical Propagation Delay of 20ns
- Gate Drive Matching of Less than 5ns
- Drives a 2.2nF Load with 15ns Rise Time and 12ns Fall Time at 12V VDD
- TTL-Compatible Input
- Quiescent Current of Less than 150 μ A
- UVLO for Both High Side and Low Side
- QFN-10 (4mmx4mm) and SOIC-8 Packages

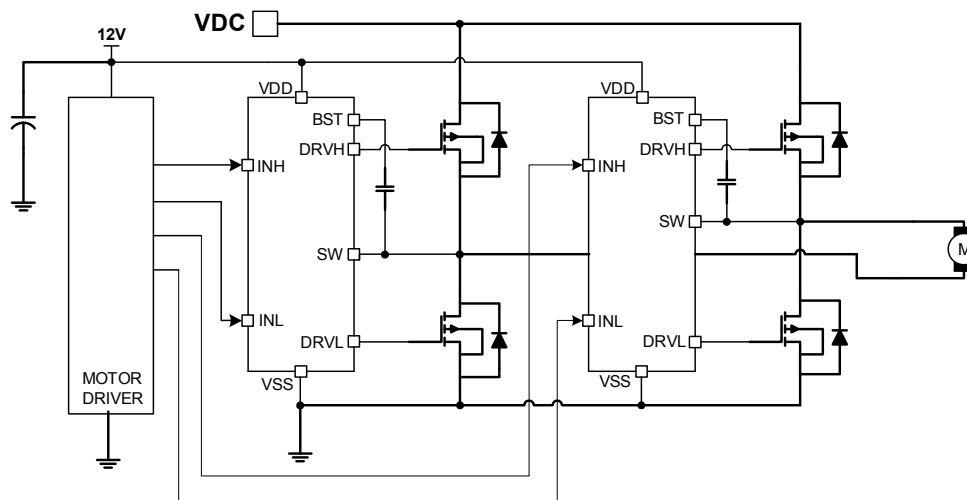
APPLICATIONS

- Motor Drivers
- Telecom Half-Bridge Power Supplies
- Avionics DC-DC Converters
- Two-Switch Forward Converters
- Active-Clamp Forward Converters

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TYPICAL APPLICATION



ORDERING INFORMATION

Part Number	Package	Top Marking
MP1924HR*	QFN-10 (4x4mm)	See Below
MP1924HS**	SOIC-8	See Below

* For Tape & Reel, add suffix -Z (e.g. MP1924HR-Z)
 For RoHS compliant packaging, add suffix -LF (e.g. MP1924HR-LF-Z)
 ** For Tape & Reel, add suffix -Z (e.g. MP1924HS-Z)
 For RoHS compliant packaging, add suffix -LF (e.g. MP1924HS-LF-Z)

TOP MARKING (MP1924HR)

MPSYWW

MP1924

LLLLLL

MPS: MPS prefix;
 Y: year code;
 WW: week code;
 MP1924: product code of MP1924HR;
 LLLLLL: lot number;

TOP MARKING (MP1924HS)

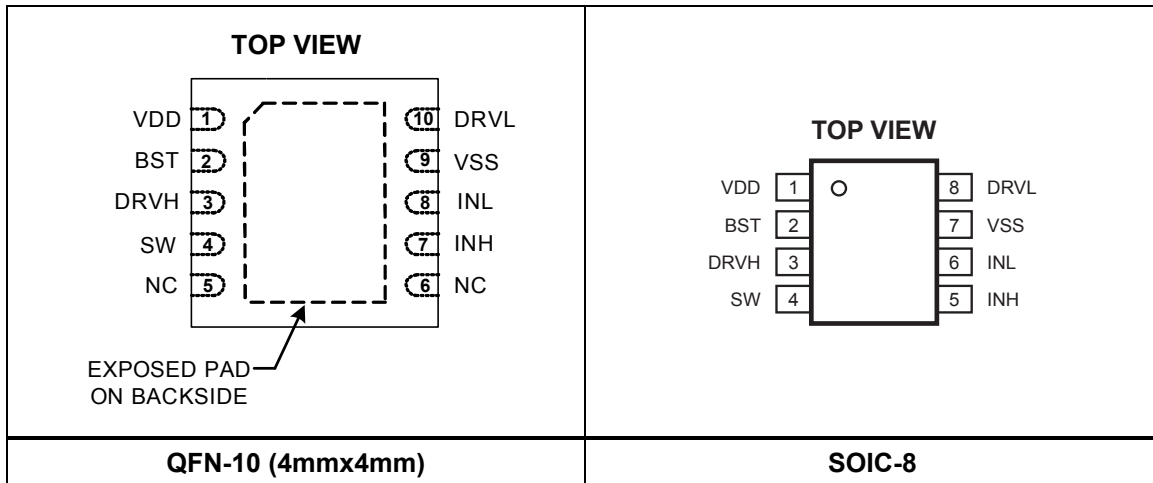
MP1924

LLLLLLLLL

MPSYWW

MP1924: product code of MP1924HS;
 LLLLLLLL: lot number;
 MPS: MPS prefix;
 Y: year code;
 WW: week code;

PACKAGE REFERENCE



Absolute Maximum Ratings ⁽¹⁾

Supply Voltage (V_{DD})	-0.3V to 18V
SW Voltage (V_{SW})	-5.0V to 105V
BST Voltage (V_{BST})	-0.3V to 118V
BST to SW	-0.3V to 18V
DRVH to SW	-0.3V to (BST-SW) + 0.3V
DRVL to VSS	-0.3V to ($V_{DD} + 0.3V$)
All Other Pins	-0.3V to ($V_{DD} + 0.3V$)
Continuous Power Dissipation ($T_A = 25^\circ\text{C}$) ⁽²⁾	
QFN-10 (4mmx4mm)	2.66W
SOIC-8	1.3W
Junction Temperature	150°C
Lead Temperature	260°C
Storage Temperature	-65°C to 150°C

Recommended Operating Conditions ⁽³⁾

Supply Voltage V_{DD}	9.0V to 16.0V
SW Voltage (V_{SW})	-1.0V to 100V
SW Slew Rate	<50V/ns
Operating Junction Temp. (T_J)	-40°C to 125°C

Thermal Resistance ⁽⁴⁾	θ_{JA}	θ_{JC}
QFN-10 (4mmx4mm)	47	7
SOIC-8	96	45

Notes:

- 1) Exceeding these ratings may damage the device.
- 2) The maximum allowable power dissipation is a function of the maximum junction temperature $T_J(\text{MAX})$, the junction-to-ambient thermal resistance θ_{JA} , and the ambient temperature T_A . The maximum allowable continuous power dissipation at any ambient temperature is calculated by $P_D(\text{MAX}) = (T_J(\text{MAX}) - T_A) / \theta_{JA}$. Exceeding the maximum allowable power dissipation will cause excessive die temperature, and the regulator will go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- 3) The device is not guaranteed to function outside of its operating conditions.
- 4) Measured on JESD51-7, 4-layer PCB.

ELECTRICAL CHARACTERISTICS

$V_{DD} = V_{BST} - V_{SW} = 12V$, $V_{SS} = V_{SW} = 0V$, No load at DRVH and DRVL, $T_A = +25^\circ C$, unless otherwise noted.

Parameter	Symbol	Condition	Min	Typ	Max	Units
Supply Currents						
VDD quiescent current	I_{DDQ}	INL = INH = 0		100	150	μA
VDD operating current	I_{DDO}	fsw = 500kHz		9		mA
Floating driver quiescent current	I_{BSTQ}	INL = INH = 0		60	90	μA
Floating driver operating current	I_{BSTO}	fsw = 500kHz		7.5		mA
Leakage current	I_{LK}	BST = SW = 100V		0.05	1	μA
Inputs						
INL/INH High				2	2.4	V
INL/INH Low			1	1.4		V
INL/INH internal pull-down resistance	R_{IN}			185		k Ω
Under Voltage Protection						
VDD rising threshold	V_{DDR}		8.1	8.4	8.8	V
VDD hysteresis	V_{DDH}			0.5		V
(BST-SW) rising threshold	V_{BSTR}		6.9	7.3	7.7	V
(BST-SW) hysteresis	V_{BSTH}			0.55		V
Bootstrap Diode						
Bootstrap diode VF @ 100 μA	V_{F1}			0.5		V
Bootstrap diode VF @ 100mA	V_{F2}			0.95		V
Bootstrap diode dynamic R	R_D	@ 100mA		2		Ω
Low Side Gate Driver						
Low level output voltage	V_{OLL}	$I_O = 100mA$		0.08		V
High level output voltage to rail	V_{OHL}	$I_O = -100mA$		0.23		V
Source Current ⁽⁵⁾	I_{OHL}	$V_{DRVL} = 0V, V_{DD} = 12V$		3		A
		$V_{DRVL} = 0V, V_{DD} = 16V$		4.7		A
Sink Current ⁽⁵⁾	I_{OLL}	$V_{DRVL} = V_{DD} = 12V$		4.5		A
		$V_{DRVL} = V_{DD} = 16V$		6		A
Floating Gate Driver						
Low level output voltage	V_{OLH}	$I_O = 100mA$		0.08		V
High level output voltage to rail	V_{OHH}	$I_O = -100mA$		0.23		V
Source Current ⁽⁵⁾	I_{OHH}	$V_{DRVH} = 0V, V_{DD} = 12V$		2.6		A
		$V_{DRVH} = 0V, V_{DD} = 16V$		4		A
Sink Current ⁽⁵⁾	I_{OLH}	$V_{DRVH} = V_{DD} = 12V$		4.5		A
		$V_{DRVH} = V_{DD} = 16V$		5.9		A

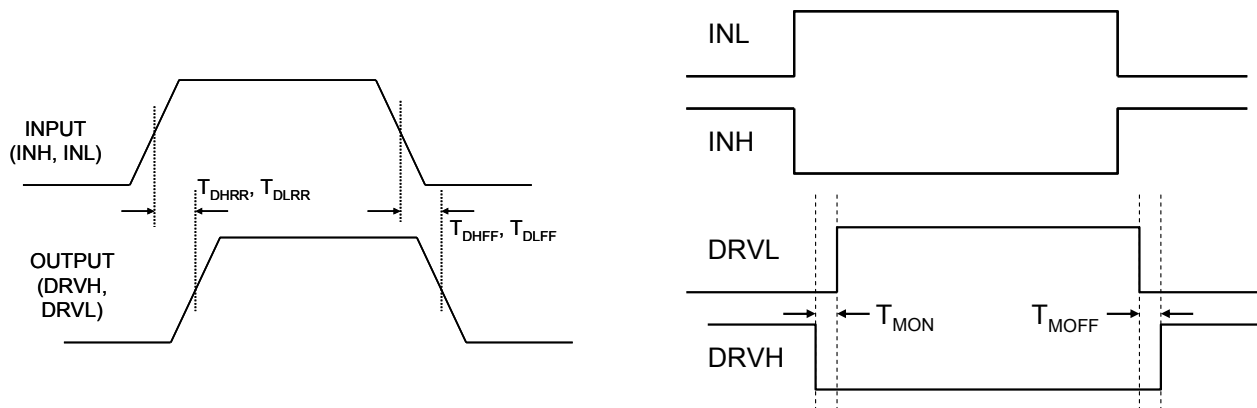
ELECTRICAL CHARACTERISTICS *(continued)*

$V_{DD} = V_{BST} - V_{SW} = 12V$, $V_{SS} = V_{SW} = 0V$, No load at DRVH and DRVL, $T_A = +25^\circ C$, unless otherwise noted.

Parameter	Symbol	Condition	Min	Typ	Max	Units
Switching Spec. --- Low Side Gate Driver						
Turn-off propagation delay INL falling to DRVL falling	T_{DLFF}			20		ns
Turn-on propagation delay INL rising to DRVL rising	T_{DLRR}			20		
DRVL rise time		$C_L = 2.2nF$		15		ns
DRVL fall time		$C_L = 2.2nF$		9		ns
Switching Spec. --- Floating Gate Driver						
Turn-off propagation delay INH falling to DRVH falling	T_{DHFF}			20		ns
Turn-on propagation delay INH rising to DRVH rising	T_{DHRR}			20		ns
DRVH rise time		$C_L = 2.2nF$		15		ns
DRVH fall time		$C_L = 2.2nF$		12		ns
Switching Spec. --- Matching						
Floating driver turn-off to low side drive turn-on ⁽⁵⁾	T_{MON}			1	5	ns
Low side driver turn-off to floating driver turn-on ⁽⁵⁾	T_{MOFF}			1	5	ns
Minimum input pulse width that changes the output ⁽⁵⁾	T_{PW}				50	ns
Bootstrap diode turn-on or turn- off time ⁽⁵⁾	T_{BS}			10		ns
Thermal shutdown				150		$^\circ C$
Thermal shutdown hysteresis				25		$^\circ C$

Note:

5) Guaranteed by design.

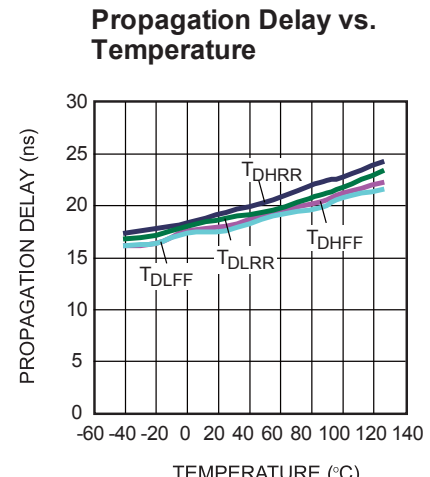
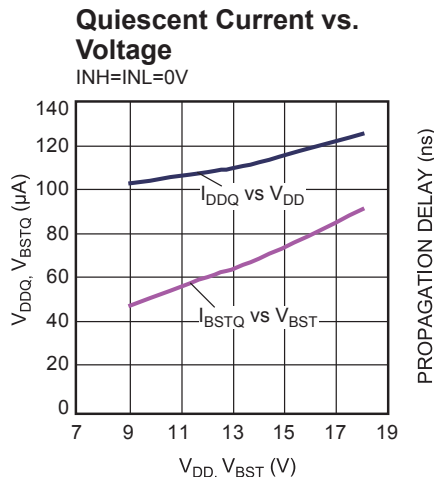
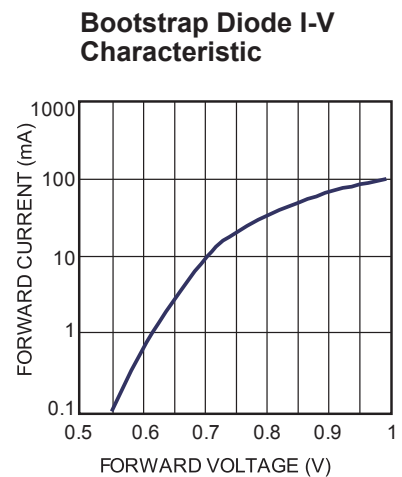
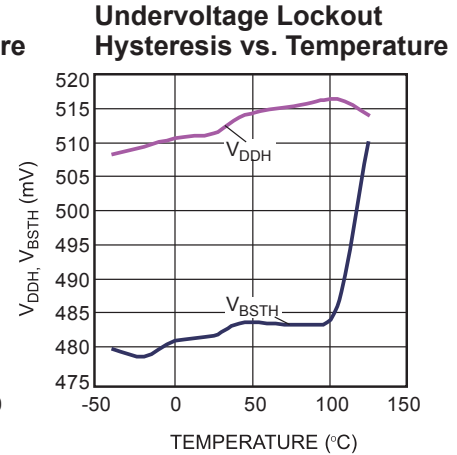
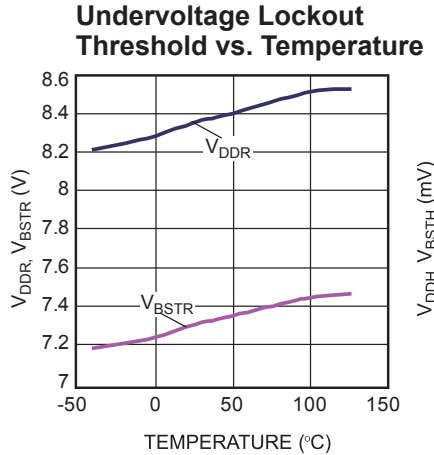
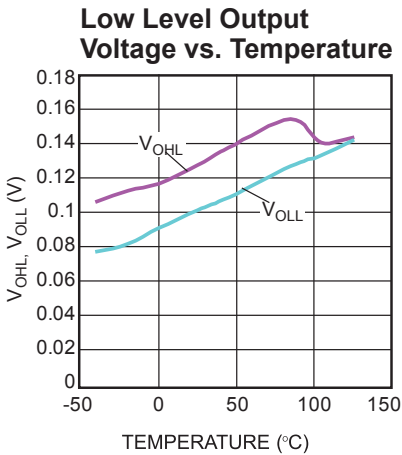
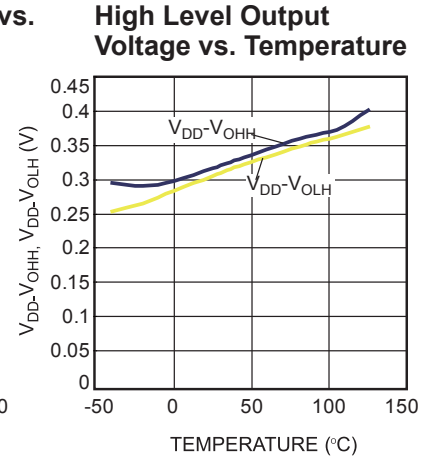
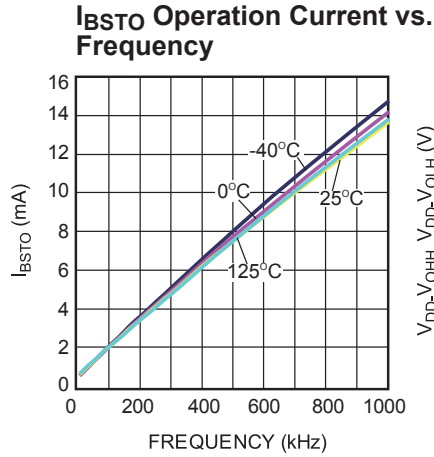
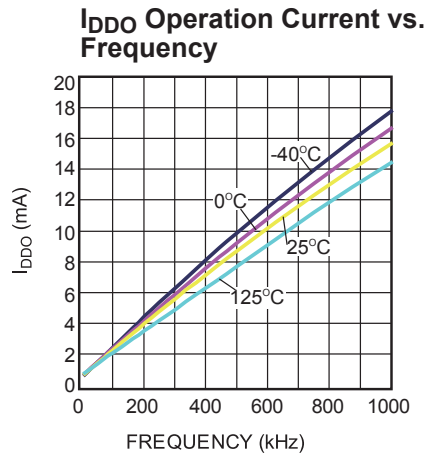

Figure 1: Timing Diagram

PIN FUNCTIONS

QFN4x4-10 Pin #	SOIC-8 Pin #	Name	Description
1	1	VDD	Supply input. This pin supplies power to all the internal circuitry. Place a decoupling capacitor to ground close to this pin to ensure stable and clean supply.
2	2	BST	Bootstrap. This is the positive power supply for the internal floating high-side MOSFET driver. Connect a bypass capacitor between this pin and SW pin.
3	3	DRVH	Floating driver output.
4	4	SW	Switching node.
5, 6		NC	No connection.
7	5	INH	Control signal input for the floating driver.
8	6	INL	Control signal input for the low side driver.
9	7	VSS, exposed pad	Chip ground. Connect exposed pad to VSS for proper thermal operation.
10	8	DRVL	Low side driver output.

TYPICAL PERFORMANCE CHARACTERISTICS

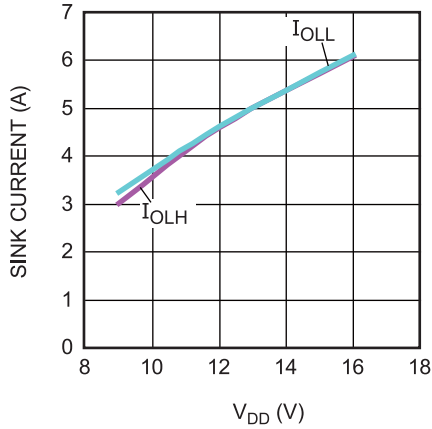
$V_{DD} = 12V$, $V_{SS} = V_{SW} = 0V$, $T_A = +25^\circ C$, unless otherwise noted.



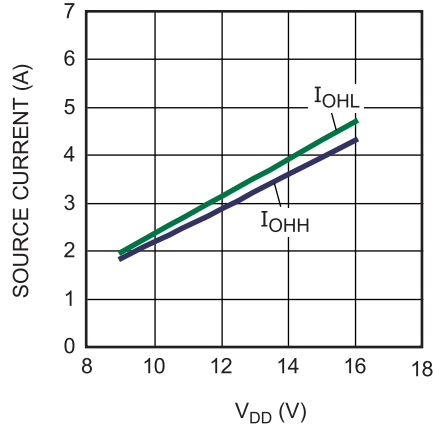
TYPICAL PERFORMANCE CHARACTERISTICS *(continued)*

$V_{DD} = 12V$, $V_{SS} = V_{SW} = 0V$, $T_A = +25^\circ C$, unless otherwise noted.

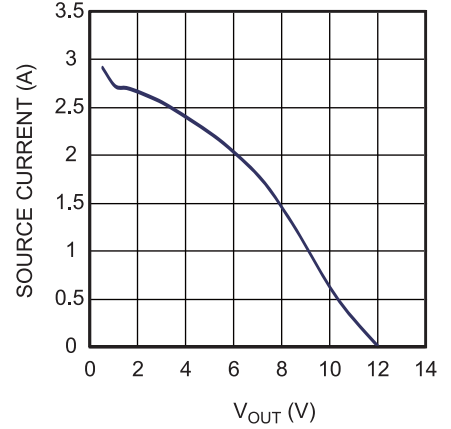
Sink Current vs. V_{DD} Voltage



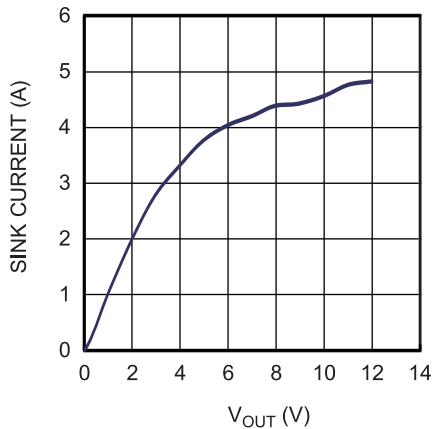
Source Current vs. V_{DD} Voltage



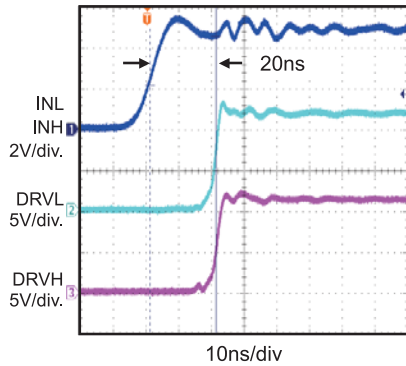
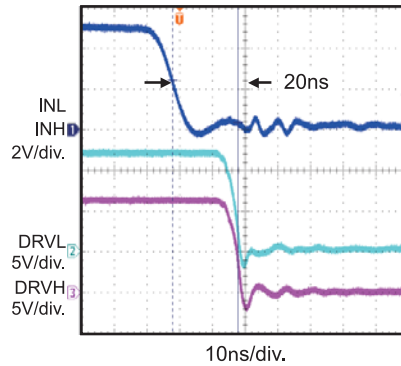
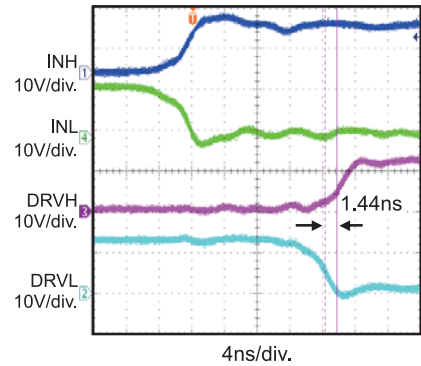
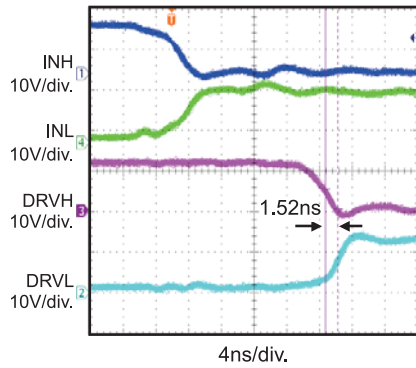
Source Current vs. Output Voltage
 $V_{DD} = 12V$



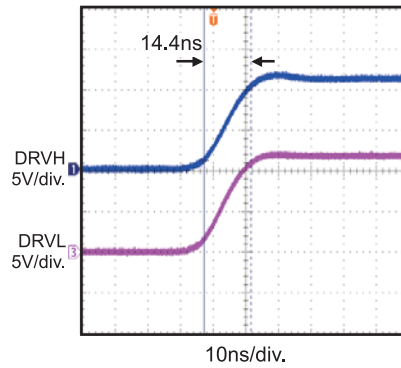
Sink Current vs. Output Voltage
 $V_{DD} = 12V$



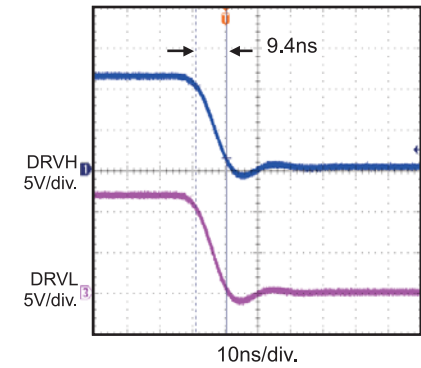
TYPICAL PERFORMANCE CHARACTERISTICS (continued)
 $V_{DD} = 12V, V_{SS} = V_{SW} = 0V, T_A = +25^\circ C$, unless otherwise noted.

Turn-on Propagation Delay

Turn-off Propagation Delay

Gate Drive Matching T_{MOFF}

Gate Drive Matching T_{MON}

Drive Rise Time

2.2nF Load


Drive Fall Time

2.2nF Load



BLOCK DIAGRAM

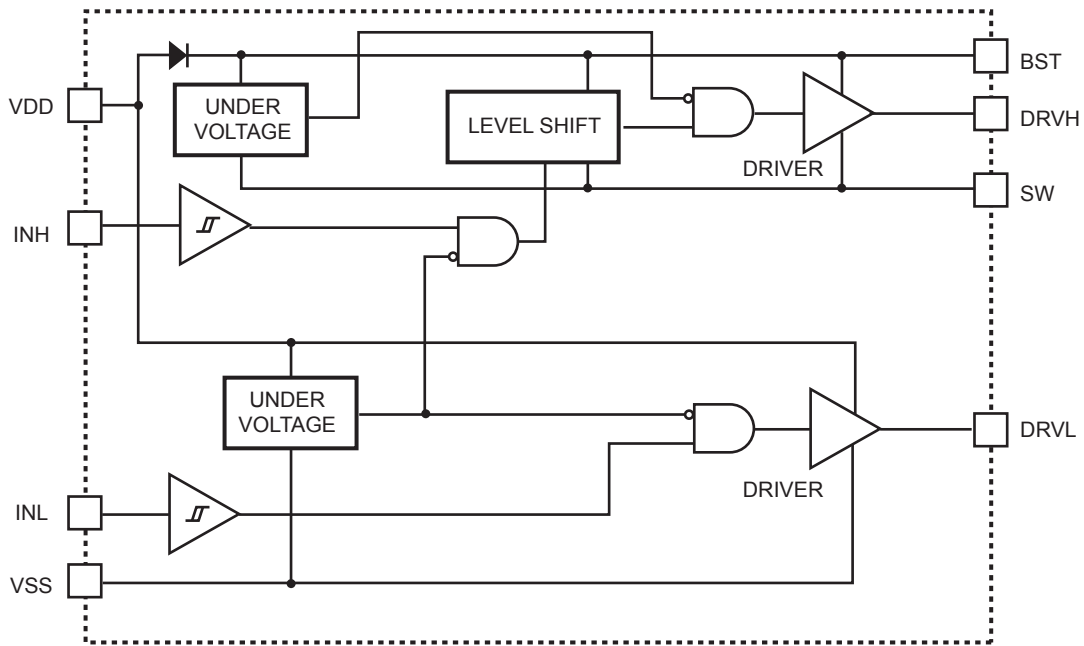


Figure 2: Function Block Diagram

APPLICATION

The input signals of INH and INL can be controlled independently. If both INH and INL control the high-side MOSFET and low-side MOSFET of the same bridge, then users must avoid shoot through by

setting sufficient dead time between INH and INL low, and vice versa. See Figure 3 below. Dead time is defined as the time interval between INH low and INL low.

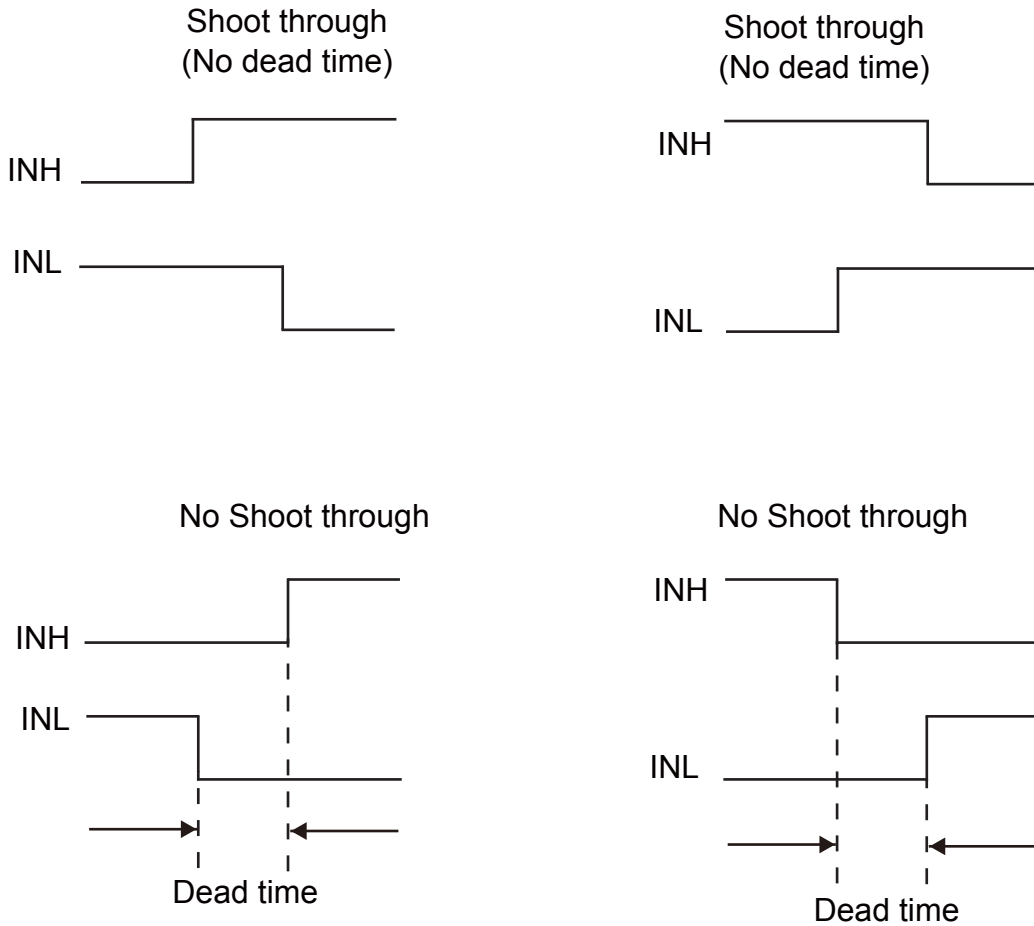


Figure 3: Shoot-Through Timing Diagram

REFERENCE DESIGN CIRCUITS

Half Bridge Converter

The MP1924 drives the MOSFETs with alternating signals (with dead time) in half-bridge converter topology. Therefore, from the PWM

controller drives INH and INL with alternating signals the input voltage can go up to 100V.

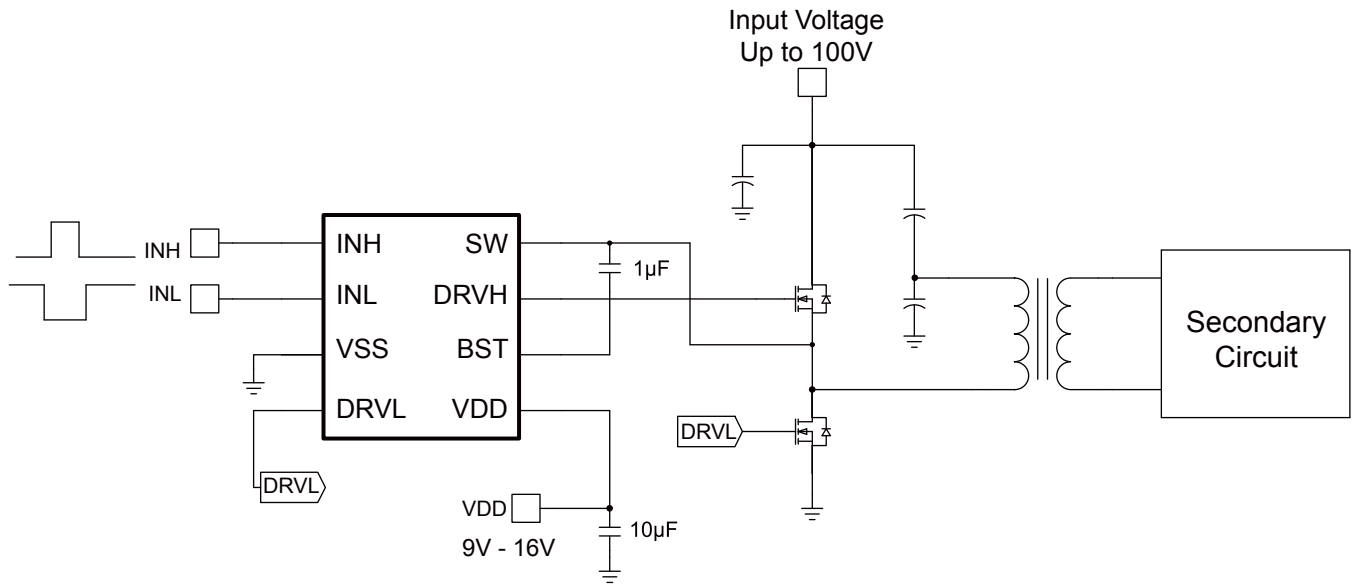


Figure 4: Half Bridge Converter

Two-Switch Forward Converter

In two-switch forward converter topology, both MOSFETs are turned on and off simultaneously. The input signal (INH and INL) comes from a PWM controller that senses the output voltage (and output current during current-mode control).

The Schottky diodes clamp the reverse swing of the power transformer and must be rated for the input voltage. The input voltage can go up to 100V.

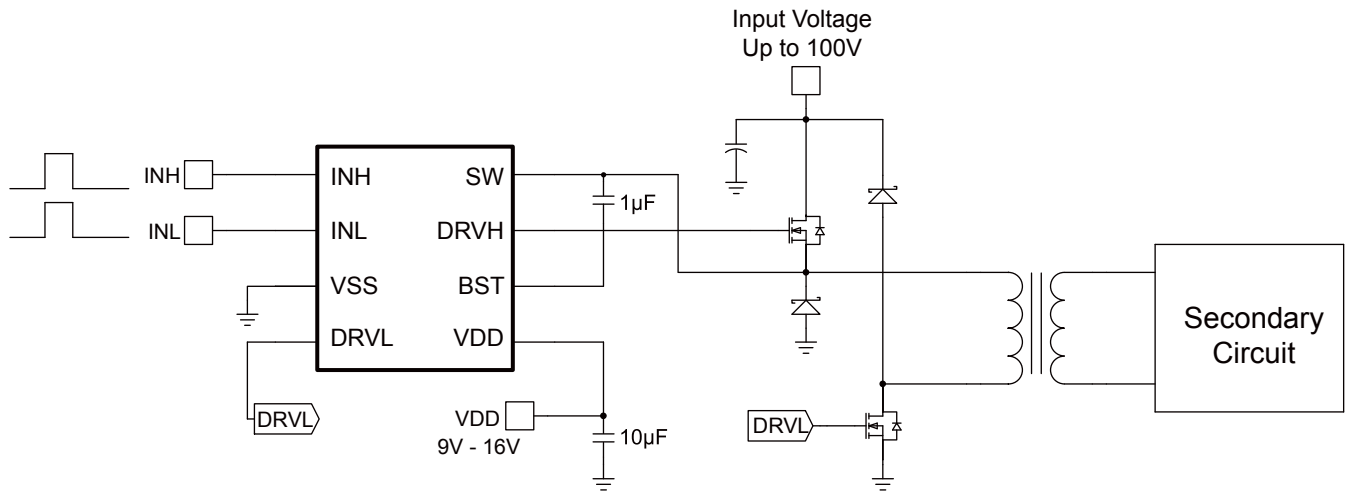


Figure 5: Two-Switch Forward Converter

Active-Clamp Forward Converter

In active-clamp forward converter topology, the MP1924 drives the MOSFETs with alternating signals. The high-side MOSFET, in conjunction with C_{reset} , is used to reset the power transformer in a lossless manner.

This topology lends itself well to run at duty cycles exceeding 50%. The device may not be able to run at 100V under this topology.

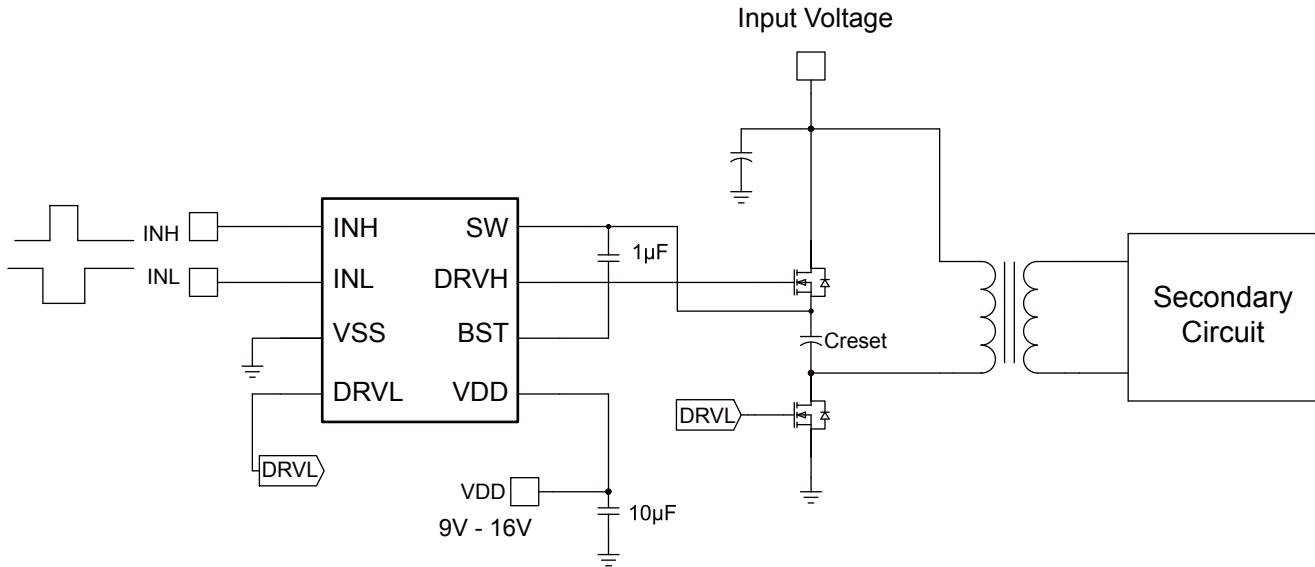
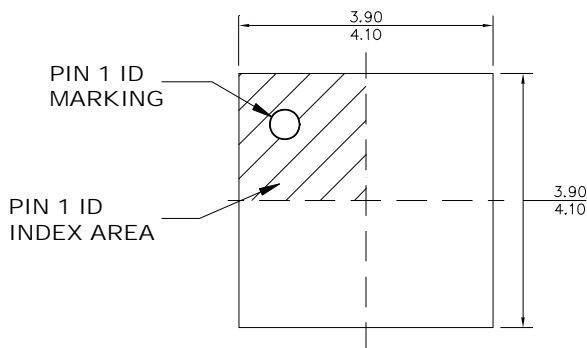


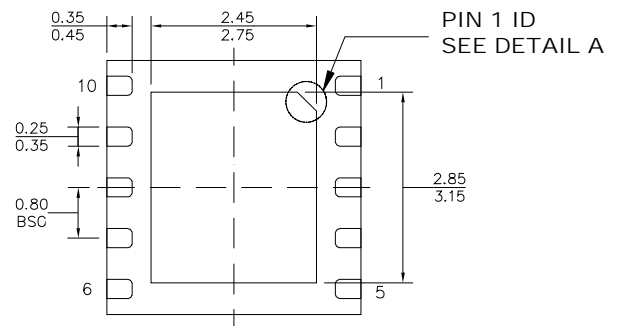
Figure 6 Active-Clamp Forward Converter

PACKAGE INFORMATION

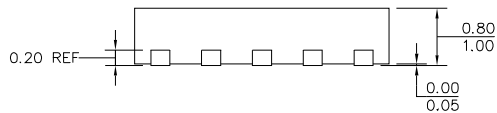
QFN-10 (4mm×4mm)



TOP VIEW

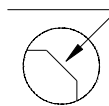


BOTTOM VIEW

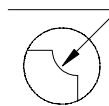


SIDE VIEW

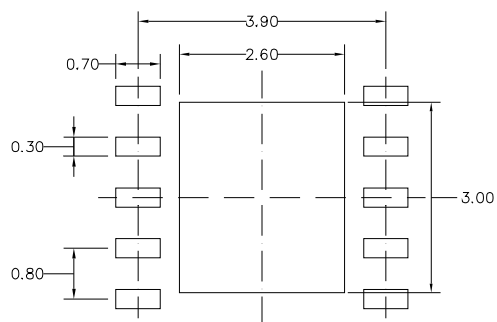
PIN 1 ID OPTION A
0.30x45° TYP.



PIN 1 ID OPTION B
R0.25 TYP.



DETAIL A

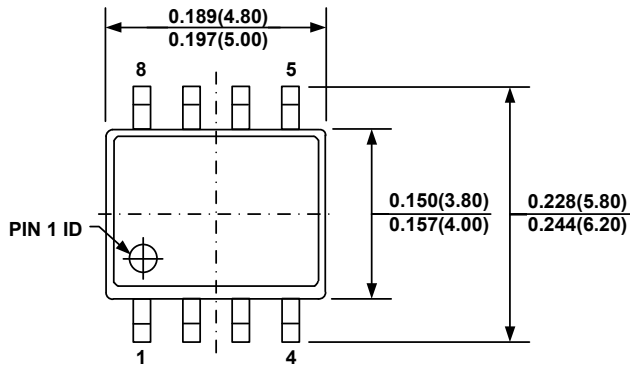


RECOMMENDED LAND PATTERN

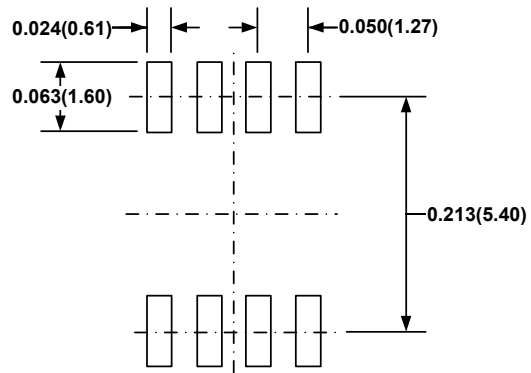
NOTE:

- 1) ALL DIMENSIONS ARE IN MILLIMETERS.
- 2) EXPOSED PADDLE SIZE DOES NOT INCLUDE MOLD FLASH.
- 3) LEAD COPLANARITY SHALL BE 0.10 MILLIMETERS MAX.
- 4) JEDEC REFERENCE IS MO-220.
- 5) DRAWING IS NOT TO SCALE.

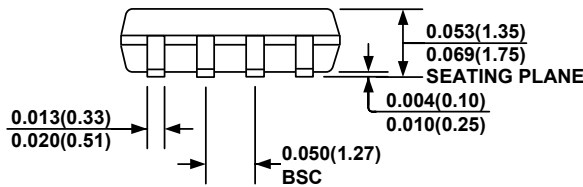
SOIC-8



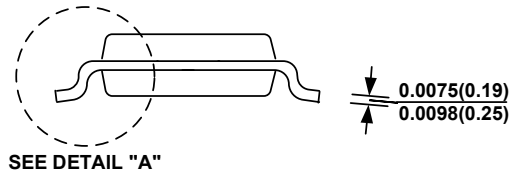
TOP VIEW



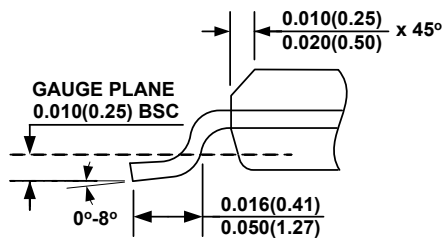
RECOMMENDED LAND PATTERN



FRONT VIEW



SIDE VIEW



DETAIL "A"

NOTE:

- 1) CONTROL DIMENSION IS IN INCHES. DIMENSION IN BRACKET IS IN MILLIMETERS.
- 2) PACKAGE LENGTH DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 3) PACKAGE WIDTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS.
- 4) LEAD COPLANARITY (BOTTOM OF LEADS AFTER FORMING) SHALL BE 0.004" INCHES MAX.
- 5) DRAWING CONFORMS TO JEDEC MS-012, VARIATION AA.
- 6) DRAWING IS NOT TO SCALE.

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